

Title (en)  
METHOD FOR FORMING A SEMICONDUCTOR DEVICE

Title (de)  
VERFAHREN ZUR FORMUNG EINES HALBLEITERBAUELEMENTS

Title (fr)  
PROCÉDÉ DE FORMATION D'UN DISPOSITIF À SEMICONDUCTEUR

Publication  
**EP 3770955 A1 20210127 (EN)**

Application  
**EP 19188136 A 20190724**

Priority  
EP 19188136 A 20190724

Abstract (en)  
A method for forming a semiconductor device comprising a first field-effect transistor, FET, device (10) and a second FET device (20) is disclosed. The first and second FET devices are formed from a first stack (112) and a second stack (112) comprising a channel material arranged on a sacrificial material. The method includes forming first spacers (116) at sidewalls of the first and second stacks, and forming a second spacer (120) between the first spacers. After recessing of the sacrificial material and removal of the first spacers, gate structures may be formed, wrapping around the at least partly released channel portions, wherein the gate structure of the first transistor device is separated from the gate structure of the second transistor device by the second spacer.

IPC 8 full level  
**H01L 21/8234** (2006.01); **H01L 21/8238** (2006.01); **H01L 29/66** (2006.01)

CPC (source: EP US)  
**H01L 21/823481** (2013.01 - EP); **H01L 21/823821** (2013.01 - US); **H01L 21/823828** (2013.01 - US); **H01L 21/823878** (2013.01 - EP); **H01L 27/0924** (2013.01 - US); **H01L 29/0673** (2013.01 - EP); **H01L 29/42392** (2013.01 - EP US); **H01L 29/66439** (2013.01 - EP); **H01L 29/66545** (2013.01 - US); **H01L 29/6656** (2013.01 - US); **H01L 29/6681** (2013.01 - US); **H01L 29/775** (2013.01 - EP); **H01L 29/78696** (2013.01 - EP); **B82Y 10/00** (2013.01 - EP); **H01L 21/823412** (2013.01 - EP); **H01L 21/823842** (2013.01 - EP)

Citation (search report)

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Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**EP 3770955 A1 20210127**; **EP 3770955 B1 20230705**; US 11367662 B2 20220621; US 2021028068 A1 20210128

DOCDB simple family (application)  
**EP 19188136 A 20190724**; US 202016938168 A 20200724